

General Description

The MAX9960 dual-flash-pin electronics/supervoltage switch matrix replaces most of the relays and switches commonly needed to connect system resources to each of two pins in a flash memory or SOC ATE system (Figure 1). The device provides seven switches per channel to select up to four independent sources: the pin electronics (PE), two parametric measurement units (PMUs) or other Kelvin analog resources, and a flash memory programming supervoltage (FVHH_). The force-and-sense PMU switches are independently controlled, enabling their use to connect two non-Kelvin resources in place of each PMU or Kelvin resource. Each MAX9960 contains two complete seven-switch channels with fully independent controls.

The MAX9960 features signal path switches with wide 600MHz bandwidth, low 3Ω series resistance, and low 8pF shunt capacitance over a voltage range compatible with common pin electronics ICs. An on-chip voltage-doubling buffer with selectable 1x or 2x gain generates the flash supervoltage, allowing a 6.5V DAC reference input to generate up to a maximum of 13V for flash-memory programming levels.

When switching from the FV_{HH} to PE_ or from PE_ to FV_{HH}, the device-under-test (DUT_) voltage behaves monotonically. Switching transitions between the PE_ and FV_{HH}_ inputs are typically less than 350ns.

The MAX9960 operates over a commercial 0°C to +70°C temperature range, and is available in the 48-pin thin QFN package (7mm x 7mm x 0.8mm) with an exposed pad on the bottom for heat removal.

Applications

Flash Memory Automatic Test Equipment SOC Automatic Test Equipment

Features

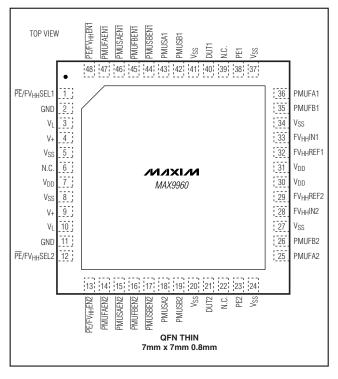
- ♦ Dual Supervoltage Switch Arrays
- ♦ 3Ω, 8pF, 600MHz Bandwidth Pin Electronics Paths
- **♦ 13V Flash Programming Paths**
- ♦ On-Chip 1x and 2x Selectable Gains
- ♦ 2 Kelvin PMU Paths
- ♦ Fast Switching: 350ns (typ)
- ♦ Monotonic Slew Rate When Switching Between PE_ and FVHH_

Ordering Information

PART	TEMP RANGE	PIN-PACKAGE*	PKG CODE
MAX9960BCTM		48 Thin QFN-EP** (7mm x 7mm x 0.8mm)	T4877-6

^{*}See full package information at the end of this data sheet. **EP = Exposed pad.

Pin Configuration



ABSOLUTE MAXIMUM RATINGS

V+ to GND	0.3V to +26V	Peak Current (100ns), PE±300mA
V _{DD} to GND	0.3V to +16.5V	Peak Current (100ns), PMUS±20mA
Vss to GND	6.5V to +0.3V	Peak Current (100ns), PMUFA_ + PMUFB_ +
V _L to GND	0.3V to +6V	(FVHH_ Path)±70mA
V+ to V _{SS}	+32V	Package Continuous Power Dissipation (T _A = +70°C)
Digital Inputs	(GND - 0.3V) to (V _L + 0.3V)	48-Pin QFN-EP, on Single-Layer Board
FV _{HH} IN	(the higher of -4V and	(derate 27.8mW/°C above +70°C)2222mW
(V _{SS} - 0.3V)) to (the	e lower of $+10V$ and $(V_{DD} + 0.3V)$)	48-Pin QFN-EP, on Multilayer Board
All Other Pins	($V_{SS} - 0.3V$) to ($V_{DD} + 0.3V$)	(derate 40.0mW/°C above +70°C)3200mW
	±120mA	Operating Temperature Range0°C to +70°C
Continuous Current, PMUS	±10mA	Junction Temperature+150°C
Continuous Current, PMUFA_		Storage Temperature Range65°C to +150°C
(FVHH_ Path)	±45mA	Lead Temperature (soldering 10s)+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V+ = +24V, V_{DD} = +15V, V_{SS} = -5V, V_L = +3.3V, T_A = +25^{\circ}C$, unless otherwise noted. Specifications at $T_A = 0^{\circ}C$ are guaranteed by design and characterization. Typical values are at $T_A = +25^{\circ}C$, unless otherwise noted.) (Figure 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
DC CHARACTERISTICS			•			
PE_ PATH						
On-Resistance	Dov	V _{DUT} = +2.5V, I _{SW} = -40mA to +40mA, T _A = 0°C to +30°C (Note 1)	2.5	3.0	3.5	0
Ori-Resistance	R _{ON}	V_{DUT} = +2.5V, Isw = -40mA to +40mA, TA = +30°C to +70°C (Note 1)	2.5		4.2	Ω
On-Resistance Flatness	R _{FLAT} (ON)	V _{DUT} _ = 0 to +5V (Note 1)	-0.6		+0.6	Ω
Ch1 to Ch2 Resistance Match	Rматсн	V_{DUT} = +2.5V, I_{SW} = -40mA to +40mA	-0.5		+0.5	Ω
Signal Voltage Range	VPE		-3.5		+8.0	V
Operating DC Current Range	Isw		-40		+40	mA
FV _{HH} _ PATH						
On-Resistance	R _{ON}	FV _{HH} _ = -1.5V to (V _{DD} - 1.5V), I _{HH} _ = -10mA to +10mA (Notes 1, 2)	32		100	Ω
Operating Voltage Range	FV _{HH} _		-1.5		V _{DD} - 1.5	V
Operating DC Current Range	Isw		-10		+10	mA
FORCE PATHS	•		•			
On-Resistance	Ron	VPMUF = -4.25V to +14.5V, IPMUF = -25mA to +25mA (Note 1)			70	Ω
Operating Voltage Range	VPMUF		-4.25		+14.5	V
Operating DC Current Range	Isw		-25		+25	mA
SENSE PATHS						
On-Resistance	Ron	V _{PMUS_} = -4.25V to +14.5V, I _{PMUS_} = -1mA to +1mA (Note 1)			1250	Ω

ELECTRICAL CHARACTERISTICS (continued)

 $(V+=+24V, V_{DD}=+15V, V_{SS}=-5V, V_L=+3.3V, T_A=+25^{\circ}C, unless otherwise noted.$ Specifications at $T_A=0^{\circ}C$ and $T_A=+70^{\circ}C$ are guaranteed by design and characterization. Typical values are at $T_A=+25^{\circ}C, unless$ otherwise noted.) (Figure 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Operating Voltage Range	V _{PMUS}		-4.25		+14.5	V
Operating DC Current Range	Isw		-1		+1	mA
FV _{HH} _ BUFFERS						
DC Output Current	lodc	$FV_{HH} = -1.5V \text{ to } (V_{DD} - 1.5V)$	10			mA
Current Limit	l	DUT_ sourcing current	+15		+25	mΛ
Current Limit	ILIM	DUT_ sinking current	-25		-15	mA
Operating Voltage Range	FV _{HH}	FV _{HH} REF_ = 0 (Note 2)	-1.5		V _{DD} - 1.5V	V
Linearity Error	LER_FVHH FVHHREF_ = 0; no load; relative to 2-point line between V _{DUT} = 0 and +13V; measured at V _{DUT} = +3.25V, +6.5V, and +9.75V		-2		+2	mV
Gain	GFV _{HH}	FV _{HH} REF_ = 0, no load, V _{DUT} _ = 0 to +13V (Note 3)	1.98	2.00	2.02	V/V
Output Offset	Vos_FV _{HH}	FV _{HH} REF_ = 0, V _{DUT} _ = +12V, no load	-50		+50	mV
Output Offset Temperature Coefficient	T _{C_VOS}	V _{DUT} = 0 to +13V, FV _{HH} REF_ = 0, T _{CASE} = +30°C to +50°C	±0.2			mV/°C
Input Bias Current	IFV _{HH}	FV _{HH} IN_ = -1.5V to +7.5V, FV _{HH} REF_ = open	-25		+25	μΑ
Gain Resistor Ground	FV _{HHREF}	(Note 4)	-1.5		+0.5	V
Gain Resistor Current	Stor Current Neasured with FV _{HH} IN_ = +5V, FV _{HH} REF_ = 0 0.4		0.4		mA	
LEAKAGE (Notes 5, 6)						
DUT_ Leakage, Disabled	I _{LEAK_OFF}	Switches S1, S2, S6, S7 open; V _{DUT} = -4.25V to +14.5V	-1		+1	nA
PE_ Leakage	ILEAK_PE	S1 closed; S2, S6, S7 open; V _{DUT} _ = -3.5V to +8V	-1		+1	nA
PMUA_ Path Leakage, Enabled	ILEAK_PMU A_ON	S2, S4, S6 closed; S1, S3, S5, S7 open; VDUT_ = -4.25V to +14.5V	-1		+1	nA
PMUB_ Path Leakage, Enabled	ILEAK_PMU B_ON	S2, S5, S7 closed; S1, S3, S4, S6 open; V _{DUT} = -4.25V to +14.5V	-1		+1	nA
PMUA_ Path Leakage, Disabled	ILEAK_PMU A_OFF	S4, S6 open; V _{PMUFA} = -4.25V to +14.5V; measured at PMUFA with PMUSA externally connected to PMUFA	-1		+1	nA
PMUB_ Path Leakage, Disabled	ILEAK_PMU B_OFF	S5, S7 open; V _{PMUFB} = -4.25V to +14.5V; measured at PMUFB with PMUSB externally connected to PMUFB			+1	nA
DIGITAL INPUTS (PMUF_EN_, P	MUS_EN_, PE	FV _{HH} EN_, PE/FV _{HH} SEL_)				
Input High Voltage	VIH		+2.3			V
Input Low Voltage	VIL				+0.4	V



ELECTRICAL CHARACTERISTICS (continued)

 $(V+ = +24V, V_{DD} = +15V, V_{SS} = -5V, V_L = +3.3V, T_A = +25^{\circ}C$, unless otherwise noted. Specifications at $T_A = 0^{\circ}C$ and $T_A = +70^{\circ}C$ are guaranteed by design and characterization. Typical values are at $T_A = +25^{\circ}C$, unless otherwise noted.) (Figure 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Voltage Range	VIN		-0.2		VL	V
Input Current	I _{IH} , I _{IL}	$V_{IN} = -0.2V$ to V_L	-10		+10	μΑ
POWER SUPPLIES						
Positive Supply	V_{DD}		14.5	15	16.0	V
Negative Supply	V _{SS}		-6.00	-5	-4.25	V
High Voltage Supply	V+	(Note 1)	23	24	25	V
Logic Supply	VL		3.0	3.3	3.6	V
Quiescent Positive Supply Current	Σ (I _{DD} , I+)	$V+=+24V,\ V_{DD}=+15V,\\ V_{SS}=-5V,\ V_L=+3.3V,\\ FV_{HH}IN_=+6.5V,\ FV_{HH}REF_=0,\\ all\ digital\ inputs=+2.3V,\ no\ loads$			10	mA
Quiescent Negative Supply Current	9 119 199				8.5	mA
Quiescent Logic Supply Current	ogic Supply Current $ V+=+24V, V_{DD}=+15V, \\ V_{SS}=-5V, V_L=+3.3V, \\ FV_{HH}IN_{-}=+6.5V, FV_{HH}REF_{-}=0, \\ all \ digital \ inputs=+2.3V, \ no \ loads $				2	mA
Quiescent Power Dissipation	$V + = +24V, V_{DD} = +15V,$ $V_{CC} = -5V, V_{L} = +3.3V$				200	mW
AC CHARACTERISTICS						
SWITCHING TIMES BETWEEN P	E_ AND FV _{HI}	 PATHS (Note 7) (Figure 3)				
Switch PE to FV _{HH}	ton Dan	+5V to +7V transition		275	425	ns
SWILETT L_ TO T VHHL	ton_fvhh	0 to +13V transition		350	500	113
FV _{HH} _ Settling Time	ts_FVHH	Settling to within larger of 1% step voltage or 50mV of final value		500		ns
Switch FV _{HH} to PE_	ton_pe			300	425	ns
PE_ Settling Time	ts_pe	Settling to within larger of 1% step voltage			ns	
PE_ TO FV _{HH} _ Overshoot/Undershoot				±100		mV
PE_ to FV _{HH} _ Preshoot				±150		mV
Minimum Switching Slew Rate	SR _{MIN}	Over 20% to 80% region		±10		V/µs
SWITCHING TIMES, SAME PATH	(Note 8) (Fig	ure 2)				
PE_ Switch On-Time	ton_1	V_{PE} = +5V from 47 Ω source		150		ns
FV _{HH} _ Switch On-Time	ton_2,3	FV _{HH} IN_ = +2.5V, FV _{HH} REF_ = 0		350		ns

ELECTRICAL CHARACTERISTICS (continued)

 $(V+=+24V,\,V_{DD}=+15V,\,V_{SS}=-5V,\,V_L=+3.3V,\,T_A=+25^{\circ}C,\,unless\,otherwise\,noted.$ Specifications at $T_A=0^{\circ}C$ and $T_A=+70^{\circ}C$ are guaranteed by design and characterization. Typical values are at $T_A=+25^{\circ}C,\,unless\,otherwise\,noted.$) (Figure 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
PMUF Switch On-Time	ton_2,4 ton_2,5	VPMUF = +5V		150		ns
PMUS Switch On-Time	tON_6 tON_7	V _{PMUS} = +5V 300				ns
PE_, FV _{HH} _, PMUF, PMUS Switch Off-Times	toff			700		ns
CAPACITANCE AND BANDWIDT	H (Note 5)					
Capacitance, All Paths Disconnected	C _{DUT_} OFF	All switches disconnected, for frequencies greater than 2MHz (Note 9)		20		рF
Capacitance, PE_ Path	0	Switch S1 closed, all others open, for frequencies greater than 2MHz		8		
Connected (Note 9)	CDUT_PE	Switch S1 closed, all others open, for frequencies less than 1kHz		50		pF
Unit-to-Unit Variation, PE_ Path Connected	ΔC _{DUT_PE}	Switch S1 closed, all others open, for frequencies greater than 2MHz (Note 9)		±2		рF
Capacitance, PMUFA_ and PMUSA_ Path Connected	CDUT_PMUA	S2, S4, and S6 closed; all others open (Note 9)	35			рF
Capacitance, PMUFB_ and PMUSB_ Path Connected	CDUT_PMUB	S2, S5, and S7 closed; all others open (Note 9)	35			рF
Capacitance, PMUFA_ Path Disconnected	C _{PMUFA_OFF}	S4 open, measured at PMUFA_ (Note 9)	10			рF
Capacitance, PMUFB_ Path Disconnected	C _{PMUFB_OFF}	S5 open, measured at PMUFB_ (Note 9)		10		pF
Capacitance, PMUSA_ Path Connected	C _{PMUSA_ON}	S6 closed, all others open, measured at PMUSA_ (Note 9)		10		рF
Capacitance, PMUSB_ Path Connected	C _{PMUSB_ON}	S7 closed, all others open, measured at PMUSB_ (Note 9)		10		pF
Capacitance, PMUSA_ Path Disconnected	C _{PMUSA_OFF}	S6 open, measured at PMUSA_ (Note 9)	9) 5			рF
Capacitance, PMUSB_ Path Disconnected	C _{PMUSB_OFF}	S7 open, measured at PMUSB_ (Note 9)	5			pF
PE_ Signal Bandwidth	f _{3DB}	Only PE_ path enabled (Note 10)		600		MHz
FV _{HH} _ BUFFER						
Slew Rate	SRFV _{HH}	FV _{HH} REF_ = 0, (gain = 2), FV _{HH} IN_ stepped from 0 to +5V and +5V to 0	±5			V/µs
Cottling	to	C _{DUT} = 200pF to within 0.1% of step voltage, after FV _{HH} IN_ changes	25			
Settling	ts	C _{DUT} = 4000pF to within 0.1% of step voltage, after FV _{HH} IN_ changes (Note 11)		50		μs



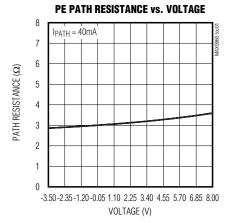
ELECTRICAL CHARACTERISTICS (continued)

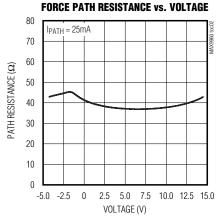
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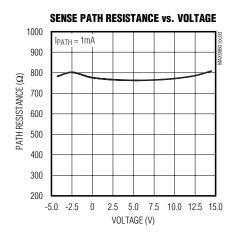
- **Note 1:** V+ should be at least 8V above V_{DD} to guarantee specified path resistance values.
- **Note 2:** When the FV_{HH} buffer is configured for a gain of +1 (FV_{HH}REF_ open), the output voltage range is limited to -1.5V to +7.5V.
- Note 3: FV_{HH}_ buffer gain is typically +1, when FV_{HH}REF_ is open.
- **Note 4:** FV_{HH}REF_ is tested by repeating the FV_{HH}_ path resistance tests over the variation of FV_{HH}REF_. For each value of FV_{HH}REF_, FV_{HH}IN_ is adjusted to FV_{HH}IN_ = (FV_{HH}_ + FV_{HH}REF_) / 2.
- Note 5: All measurements taken at DUT_, except where noted.
- **Note 6:** These specifications are guaranteed by design and characterization. In addition, these specifications will be production tested with min/max test limits of ±10nA.
- Note 7: Voltage source driving PE_ has 47Ω source resistance. PE_ = 0 to +5.0V, FV_{HH}_ = +7 to +13V. Measured from 50% point of input logic to 90% of analog swing.
- Note 8: All unused switches open, unless otherwise noted. Measured from 50% point of input logic to 90% of analog swing.
- **Note 9:** Unless otherwise noted, measured at DUT_. No external connections to any of the switched analog pins—PE_, DUT_, PMUFA_, PMUFB_, PMUSA_, or PMUSB_—except as needed to make measurement.
- Note 10: Z_{DUT} = 50Ω; equivalent bandwidth calculated from measured DUT_ rise and fall time with PE_ stimulated by a 3V step with 1ns 10% to 90% rise/fall time.
- Note 11: The maximum load for FV_{HH} buffer is 4000pF.

_Typical Operating Characteristics

 $(V + = +24V, V_{DD} = +15V, V_{SS} = -5V, V_{L} = +3.3V, T_{A} = +25^{\circ}C$, unless otherwise noted.)

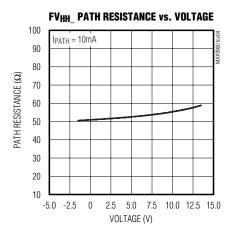


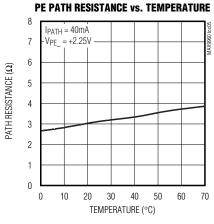


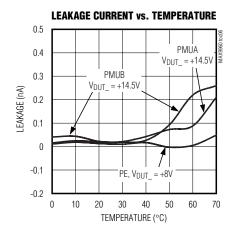


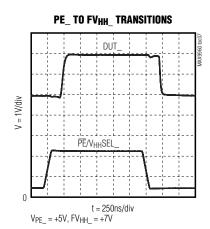
Typical Operating Characteristics (continued)

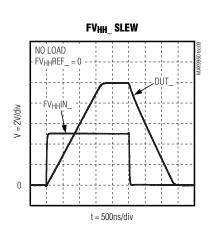
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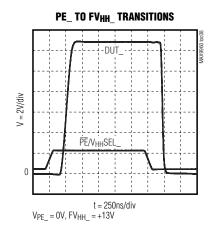


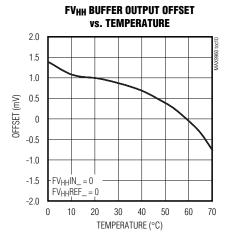












Pin Description

PIN	NAME	FUNCTION					
1	PE/FV _{HH} SEL1	PE1 or FV _{HH} 1 Select. Selects either PE1 or FV _{HH} 1 to be connected to DUT1. Force low to select PE1, force high to select FV _{HH} 1.					
2, 11	GND	round					
3, 10	VL	Logic Power Supply. Nominally 3.3V.					
4, 9	V+	Analog Positive Gate-Drive Power Supply. Nominally 24V.					
5, 8, 20, 24, 27, 34, 37, 41	V _{SS}	Analog Negative Power Supply. Nominally -5V.					
6, 22, 39	N.C.	No Connection. Make no connection to this pin.					
7, 30, 31	V_{DD}	Analog Positive Power Supply. Nominally 15V.					
12	PE/FV _{HH} SEL2	PE2 or FV _{HH} 2 Select. Selects either PE2 or FV _{HH} 2 to be connected to DUT2. Force low to select PE2, force high to select FV _{HH} 2.					
13	PE/FV _{HH} EN2	PE2 and FV _{HH} 2 Enable. Enables PE2 and FV _{HH} 2 to be connected to DUT2, as determined by PE/FV _{HH} SEL2. Force low to enable signal path, force high to disable the signal path.					
14	PMUFAEN2	PMUFA2 Enable. Controls the connection of PMUFA2 to DUT2. Force low to connect PMUFA2 to DUT2, force high to disconnect PMUFA2 from DUT2.					
15	PMUSAEN2	PMUSA2 Enable. Controls the connection of PMUSA2 to DUT2. Force low to connect PMUSA2 to DUT2, force high to disconnect PMUSA2 from DUT2.					
16	PMUFBEN2	PMUFB2 Enable. Controls the connection of PMUFB2 to DUT2. Force low to connect PMUFB2 to DUT2, force high to disconnect PMUFB2 from DUT2.					
17	PMUSBEN2	PMUSB2 Enable. Controls the connection of PMUSB2 to DUT2. Force low to connect PMUSB2 to DUT2, force high to disconnect PMUSB2 from DUT2.					
18	PMUSA2	Sense A Analog Output for Channel 2. Kelvin feedback output for the channel 2 force A path.					
19	PMUSB2	Sense B Analog Output for Channel 2. Kelvin feedback output for the channel 2 force B path.					
21	DUT2	Analog I/O for Channel 2. Connects to the DUT.					
23	PE2	Analog I/O for Channel 2. Connects to the pin electronics I/O.					
25	PMUFA2	Analog Input Force A for Channel 2. Connects to an external DC resource such as a PMU.					
26	PMUFB2	Analog Input Force B for Channel 2. Connects to an external DC resource such as a PMU.					
28	FV _{HH} IN2	Analog Supervoltage Input for Channel 2. The voltage applied to FV _{HH} IN2 is amplified as determined by FV _{HH} REF2 (see the <i>Functional Block Diagram</i>).					
29	FV _{HH} REF2	Analog Gain-Setting Input for Channel 2. Sets the gain of the FV _{HH} 2 buffer.					
32	FV _{HH} REF1	Analog Gain-Setting Input for Channel 1. Sets the gain of the FV _{HH} 1 buffer.					
33	FV _{HH} IN1	Analog Supervoltage Input for Channel 1. The voltage applied to FV _{HH} IN1 is amplified as determine by FV _{HH} REF1 (see the <i>Functional Block Diagram</i>).					
35	PMUFB1	Analog Input Force B for Channel 1. Connects to an external DC resource such as a PMU.					
36	PMUFA1	Analog Input Force A for Channel 1. Connects to an external DC resource such as a PMU.					
38	PE1	Analog I/O for Channel 1. Connects to the pin electronics I/O.					
40	DUT1	Analog I/O for Channel 1. Connects to the DUT.					
42	PMUSB1	Sense B Analog Output for Channel 1. Kelvin feedback output for the channel 1 force B path.					
43	PMUSA1	Sense A Analog Output for Channel 1. Kelvin feedback output for the channel 1 force A path.					

Pin Description (continued)

PIN	NAME	FUNCTION			
44	PMUSBEN1	PMUSB1 Enable. Controls the connection of PMUSB1 to DUT1. Force low to connect PMUSB1 to DUT1, force high to disconnect PMUSB1 from DUT1.			
45	PMUFB1 Enable. Controls the connection of PMUFB1 to DUT1. Force low to connect PMUFB1 to DUT1, force high to disconnect PMUFB1 from DUT1.				
46	PMUSAEN1	PMUSA1 Enable. Controls the connection of PMUSA1 to DUT1. Force low to connect PMUSA1 to DUT1, force high to disconnect PMUSA1 from DUT1.			
47	PMUFAEN1	PMUFA1 Enable. Controls the connection of PMUFA1 to DUT1. Force low to connect PMUFA1 to DUT1, force high to disconnect PMUFA1 from DUT1.			
48	PE/FV _{HH} EN1	PE1 and FV _{HH} 1 Enable. Enables PE1 and FV _{HH} 1 to be connected to DUT1, as determined by PE/FV _{HH} SEL1. Force low to enable signal path, force high to disable the signal path.			
_	EP	Exposed Pad for Heat Removal. Internally biased to VSS. Connect to VSS or leave floating.			

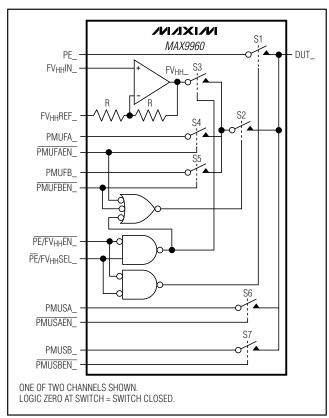


Figure 1. Functional Block Diagram

Detailed Description

The MAX9960 is a dual analog switch matrix featuring two Kelvin PMU paths, a PE path, and a flash programming supervoltage circuit that allows testing of flash memory using standard PE devices. It makes possible, without the use of relays, a fully functional pin with both AC and DC capabilities.

The signal path switches feature 600MHz bandwidth, 3Ω series resistance, and 8pF shunt capacitance over a voltage range compatible with common pin-electronics ICs. The voltage-doubling buffer, with selectable 1x or 2x gain, generates the 13V flash memory programming level from a 6.5V input. Configure the switches using digital inputs $\overline{PMUFAEN}_-$, $\overline{PMUSAEN}_-$, $\overline{PMUFBEN}_-$, $\overline{PMUSBEN}_-$, $\overline{PE/FV_{HH}EN}_-$, and $\overline{PE/FV_{HH}EN}_-$, and $\overline{PE/FV_{HH}EN}_-$, as indicated in Tables 1 and 2.

The switching speed between PE_ and FV_{HH_} paths is less than 350ns typical (Figure 3), and during switching, DUT_ behaves monotonically.

FV_{HH} Buffer Load Capacitance

The maximum load capacitance for the FV_{HH} buffer is 4000pF. While this amount of load capacitance is not expected during normal operation, an application may call for the buffer to be connected to a highly capacitive PMU path occasionally for calibration purposes. No damage to the MAX9960 will result as a consequence of this condition.

Supervoltage FV_{HH} Buffer Gain

The FV_{HH} buffer gain can be selected using FV_{HH}REF_{_}. If FV_{HH}REF_{_} is grounded, the gain of the buffer is +2. If FV_{HH}REF_{_} is left floating, the buffer gain is +1.

Table 1. Switch Control, All Possible Combinations

PMUFAEN_	PMUFBEN_	PMUSAEN_	PMUSBEN_	PE/FV _{HH} EN_	PE/FV _{HH} SEL_	DUT_
0	Χ	Χ	X	X	Χ	PMUFA_ path connected
X	0	X	X	X	X	PMUFB_ path connected
Х	Χ	0	X	X	X	PMUSA_ path connected
X	Χ	X	0	X	X	PMUSB_ path connected
Х	Χ	X	X	0	1	FV _{HH} _ path connected
X	X	X	X	0	0	PE_ path connected
		Every path is disconnected				

Table 2. Switch Control, Use Cases

PMUFAEN_	PMUFBEN_	PMUSAEN_	PMUSBEN_	PE/FV _{HH} EN_	PE/FV _{HH} SEL_	DUT_
1	1	1	1	0	0	PE_
1	1	1	1	0	1	FV _{HH} _
0	1	0	1	1	X	PMUFA_ + PMUSA_
1	0	1	0	1	X	PMUFB_ + PMUSB_
0	1	0	1	0	0	PE_ + PMUFA_ + PMUSA_
1	0	1	0	0	0	PE_ + PMUFB_ + PMUSB_
0	1	0	1	0	1	FV _{HH} _ + PMUFA_ + PMUSA_
1	0	1	0	0	1	FV _{HH} _ + PMUFB_ + PMUSB_
0	0	0	0	0	0	PE_ + PMUFA_ + PMUSA_ + PMUFB_ + PMUSB_

Power-Supply Considerations

The MAX9960 requires four power-supply voltages, typically V+ = +24V, V_{DD} = +15V, V_{SS} = -5V, and V_{L} = +3.3V. Use a 0.1µF bypass capacitor close to each supply pin, and provide bulk bypassing where power enters the circuit board. The MAX9960 does not require any special power-up sequencing.

Chip Information

TRANSISTOR COUNT: 2020

PROCESS: BICMOS

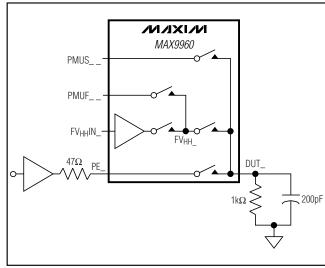


Figure 2. Switching Time Test Circuit

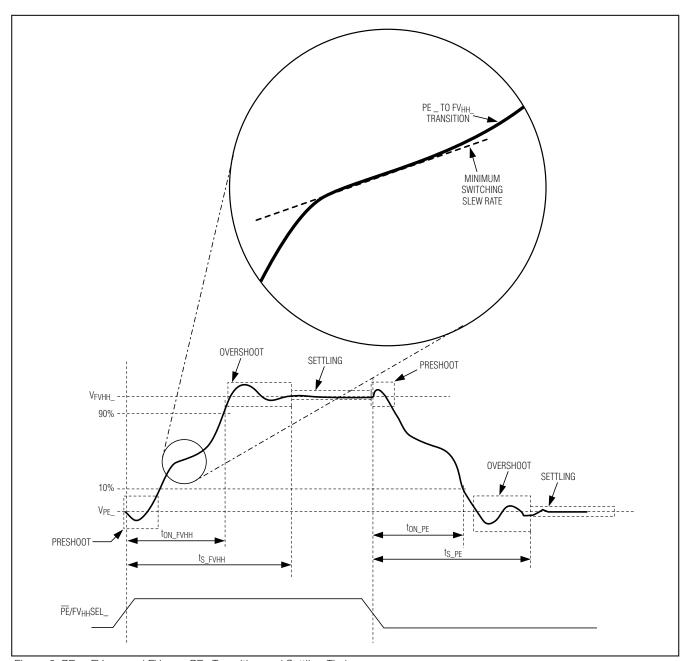


Figure 3. PE_ - FV_{HH}_ and FV_{HH}_ - PE_ Transition and Settling Timing

Package Information

For the latest package outline information, go to www.maxim-ic.com/packages.

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